AMD Xilinx - XC6VHX380T-1FFG1923C Datasheet

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Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications,

Details	
Product Status	Active
Number of LABs/CLBs	29880
Number of Logic Elements/Cells	382464
Total RAM Bits	28311552
Number of I/O	720
Number of Gates	-
Voltage - Supply	0.95V ~ 1.05V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	1924-BBGA, FCBGA
Supplier Device Package	1924-FCBGA (45x45)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xc6vhx380t-1ffg1923c

Table 2: **Recommended Operating Conditions**

Symbol	Description	Min	Max	Units
V_{CCINT}	Internal supply voltage relative to GND for all devices except -1L devices.	0.95	1.05	V
	For -1L commercial temperature range devices: internal supply voltage relative to GND, T_j = 0°C to +85°C	0.87	0.93	V
	For -1L industrial temperature range devices: internal supply voltage relative to GND, T_j = –40°C to +100°C	0.91	0.97	V
V_{CCAUX}	Auxiliary supply voltage relative to GND	2.375	2.625	V
V_{CCO}(1)(2)(3)	Supply voltage relative to GND	1.14	2.625	V
V_{IN}	2.5V supply voltage relative to GND	GND – 0.20	2.625	V
	2.5V and below supply voltage relative to GND	GND – 0.20	V_{CCO} + 0.2	V
I_{IN}(5)	Maximum current through any pin in a powered or unpowered bank when forward biasing the clamp diode.	–	10	mA
V_{BATT}(6)	Battery voltage relative to GND	1.0	2.5	V
V_{FS}(7)	External voltage supply for eFUSE programming	2.375	2.625	V
T_j	Junction temperature operating range for commercial (C) temperature devices	0	85	°C
	Junction temperature operating range for extended (E) temperature devices	0	100	°C
	Junction temperature operating range for industrial (I) temperature devices	–40	100	°C
	Junction temperature operating range for military (M) temperature devices	–55	125	°C

Notes:

1. Configuration data is retained even if V_{CCO} drops to 0V.
2. Includes V_{CCO} of 1.2V, 1.5V, 1.8V, and 2.5V.
3. The configuration supply voltage V_{CC_CONFIG} is also known as V_{CCO_0}.
4. All voltages are relative to ground.
5. A total of 100 mA per bank should not be exceeded.
6. V_{BATT} is required only when using bitstream encryption. If battery is not used, connect V_{BATT} to either ground or V_{CCAUX}.
7. During eFUSE programming, V_{FS} must be within the recommended operating range and T_j = +15°C to +85°C. Otherwise, V_{FS} can be connected to GND.

Table 3: **DC Characteristics Over Recommended Operating Conditions** (1)(2)

Symbol	Description	Min	Typ	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost)	0.75	–	–	V
V_{DRI}	Data retention V_{CCAUX} voltage (below which configuration data might be lost)	2.0	–	–	V
I_{REF}	V_{REF} leakage current per pin	–	–	10	µA
I_L	Input or output leakage current per pin (sample-tested)	–	–	10	µA
C_{IN}(3)	Die input capacitance at the pad	–	–	8	pF
I_{RPU}	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 2.5V	20	–	80	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.8V	8	–	40	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.5V	5	–	30	µA
	Pad pull-up (when selected) @ V_{IN} = 0V, V_{CCO} = 1.2V	1	–	20	µA
I_{RPD}	Pad pull-down (when selected) @ V_{IN} = 2.5V	3	–	80	µA
I_{BATT}	Battery supply current	–	–	150	nA
n	Temperature diode ideality factor	–	1.0002	–	n
r	Series resistance	–	5	–	Ω

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. Maximum value specified for worst case process at 25°C.
3. This measurement represents the die capacitance at the pad, not including the package.

Power-On Power Supply Requirements

Xilinx FPGAs require a certain amount of supply current during power-on to insure proper device initialization. The actual current consumed depends on the power-on sequence and ramp rate of the power supply.

The recommended power-on sequence for Virtex-6 devices is V_{CCINT}, V_{CCAUX}, and V_{CCO} to meet the power-up current requirements listed in Table 5. V_{CCINT} can be powered up or down at any time, but power up current specifications can vary from Table 5. The device will have no physical damage or reliability concerns if V_{CCINT}, V_{CCAUX}, and V_{CCO} sequence cannot be followed.

If the recommended power-up sequence cannot be followed and the I/Os must remain 3-stated throughout configuration, then V_{CCAUX} must be powered prior to V_{CCO} or V_{CCAUX} and V_{CCO} must be powered by the same supply. Similarly, for power-down, the reverse V_{CCAUX} and V_{CCO} sequence is recommended if the I/Os are to remain 3-stated.

The GTH transceiver supplies must be powered using a MGTHAVCC, MGTHAVCCRX, MGTHAVCCPLL, and MGTHAVTT sequence. There are no sequencing requirement for these supplies with respect to the other FPGA supply voltages. For more detail see Table 27: *GTH Transceiver Power Supply Sequencing*. There are no sequencing requirements for the GTX transceivers power supplies.

Table 5 shows the minimum current, in addition to I_{CCQ}, that are required by Virtex-6 devices for proper power-on and configuration. If the current minimums shown in Table 4 and Table 5 are met, the device powers on after all three supplies have passed through their power-on reset threshold voltages. The FPGA must be configured after applying V_{CCINT}, V_{CCAUX}, and V_{CCO} for the appropriate configuration banks. Once initialized and configured, use the XPE tools to estimate current drain on these supplies.

Table 5: **Power-On Current for Virtex-6 Devices**

Device	$I_{CCINTMIN}$	$I_{CCAUXMIN}$	I_{CCOMIN}	Units
	Typ(1)	Typ(1)	Typ(1)	
XC6VLX75T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 10	I_{CCOQ} + 30 mA per bank	mA
XC6VLX130T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 10	I_{CCOQ} + 30 mA per bank	mA
XC6VLX195T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 40	I_{CCOQ} + 30 mA per bank	mA
XC6VLX240T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 40	I_{CCOQ} + 30 mA per bank	mA
XC6VLX365T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 40	I_{CCOQ} + 30 mA per bank	mA
XC6VLX550T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 40	I_{CCOQ} + 30 mA per bank	mA
XC6VLX760	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 40	I_{CCOQ} + 30 mA per bank	mA
XC6VSX315T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 40	I_{CCOQ} + 30 mA per bank	mA
XC6VSX475T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 50	I_{CCOQ} + 30 mA per bank	mA
XC6VHX250T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 40	I_{CCOQ} + 30 mA per bank	mA
XC6VHX255T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 40	I_{CCOQ} + 30 mA per bank	mA
XC6VHX380T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 40	I_{CCOQ} + 30 mA per bank	mA
XC6VHX565T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 40	I_{CCOQ} + 30 mA per bank	mA
XQ6VLX130T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 100	I_{CCOQ} + 30 mA per bank	mA
XQ6VLX240T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 100	I_{CCOQ} + 30 mA per bank	mA
XQ6VLX550T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 100	I_{CCOQ} + 30 mA per bank	mA
XQ6VSX315T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 100	I_{CCOQ} + 40 mA per bank	mA
XQ6VSX475T	See I_{CCINTQ} in Table 4	I_{CCAUXQ} + 100	I_{CCOQ} + 40 mA per bank	mA

Notes:

1. Typical values are specified at nominal voltage, 25°C.
2. Use the XPower Estimator (XPE) spreadsheet tool (download at http://www.xilinx.com/power) to calculate maximum power-on currents.

HT DC Specifications (HT_25)

Table 8: **HT DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OD}	Differential Output Voltage for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	480	600	885	mV
	Differential Output Voltage for XQ devices		480	600	930	mV
Δ V_{OD}	Change in V_{OD} Magnitude		–15	–	15	mV
V_{OCM}	Output Common Mode Voltage	R_T = 100 Ω across Q and $\overline{Q}$ signals	440	600	760	mV
Δ V_{OCM}	Change in V_{OCM} Magnitude		–15	–	15	mV
V_{ID}	Input Differential Voltage		200	600	1000	mV
Δ V_{ID}	Change in V_{ID} Magnitude		–15	–	15	mV
V_{ICM}	Input Common Mode Voltage		440	600	780	mV
Δ V_{ICM}	Change in V_{ICM} Magnitude		–15	–	15	mV

LVDS DC Specifications (LVDS_25)

Table 9: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.675	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.825	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	R_T = 100 Ω across Q and $\overline{Q}$ signals	247	350	600	mV
V_{OCM}	Output Common-Mode Voltage for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.075	1.250	1.425	V
	Output Common-Mode Voltage for XQ devices		1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High		100	350	600	mV
V_{ICM}	Input Common-Mode Voltage		0.3	1.2	2.2	V

Extended LVDS DC Specifications (LVDSEXT_25)

Table 10: **Extended LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO}	Supply Voltage		2.38	2.5	2.63	V
V_{OH}	Output High Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	–	–	1.785	V
V_{OL}	Output Low Voltage for Q and $\overline{Q}$	R_T = 100 Ω across Q and $\overline{Q}$ signals	0.715	–	–	V
V_{ODIFF}	Differential Output Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	350	–	840	mV
	Differential Output Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High for XQ devices		350	–	850	mV
V_{OCM}	Output Common-Mode Voltage for XC devices	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.075	1.250	1.425	V
	Output Common-Mode Voltage for XQ devices		1.000	1.250	1.425	V
V_{IDIFF}	Differential Input Voltage (Q – $\overline{Q}$), Q = High ($\overline{Q}$ – Q), $\overline{Q}$ = High	Common-mode input voltage = 1.25V	100	–	1000	mV
V_{ICM}	Input Common-Mode Voltage	Differential input voltage = ±350 mV	0.3	1.2	2.2	V

Table 23: **GTX Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTXTX}	Serial data rate range		0.480	–	F_{GTXMAX}	Gb/s
T_{RTX}	TX Rise time	20%–80%	–	120	–	ps
T_{FTX}	TX Fall time	80%–20%	–	120	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	350	ps
$V_{TXOOBVDPP}$	Electrical idle amplitude		–	–	15	mV
$T_{TXOOBTRANSITION}$	Electrical idle transition time		–	–	75	ns
$TJ_{6.5}$	Total Jitter(2)(3)	6.5 Gb/s	–	–	0.33	UI
$DJ_{6.5}$	Deterministic Jitter(2)(3)		–	–	0.17	UI
$TJ_{5.0}$	Total Jitter(2)(3)	5.0 Gb/s	–	–	0.33	UI
$DJ_{5.0}$	Deterministic Jitter(2)(3)		–	–	0.15	UI
$TJ_{4.25}$	Total Jitter(2)(3)	4.25 Gb/s	–	–	0.33	UI
$DJ_{4.25}$	Deterministic Jitter(2)(3)		–	–	0.14	UI
$TJ_{3.75}$	Total Jitter(2)(3)	3.75 Gb/s	–	–	0.34	UI
$DJ_{3.75}$	Deterministic Jitter(2)(3)		–	–	0.16	UI
$TJ_{3.125}$	Total Jitter(2)(3)	3.125 Gb/s	–	–	0.2	UI
$DJ_{3.125}$	Deterministic Jitter(2)(3)		–	–	0.1	UI
$TJ_{3.125L}$	Total Jitter(2)(3)	3.125 Gb/s(4)	–	–	0.35	UI
$DJ_{3.125L}$	Deterministic Jitter(2)(3)		–	–	0.16	UI
$TJ_{2.5}$	Total Jitter(2)(3)	2.5 Gb/s(5)	–	–	0.20	UI
$DJ_{2.5}$	Deterministic Jitter(2)(3)		–	–	0.08	UI
$TJ_{1.25}$	Total Jitter(2)(3)	1.25 Gb/s(6)	–	–	0.15	UI
$DJ_{1.25}$	Deterministic Jitter(2)(3)		–	–	0.06	UI
TJ_{600}	Total Jitter(2)(3)	600 Mb/s	–	–	0.1	UI
DJ_{600}	Deterministic Jitter(2)(3)		–	–	0.03	UI
TJ_{480}	Total Jitter(2)(3)	480 Mb/s	–	–	0.1	UI
DJ_{480}	Deterministic Jitter(2)(3)		–	–	0.03	UI

Notes:

1. Using same REFCLK input with TXENPMAPHASEALIGN enabled for up to 12 consecutive transmitters (three fully populated GTX Quads).
2. Using PLL_DIVSEL_FB = 2, 20-bit internal data width. These values are NOT intended for protocol specific compliance determinations.
3. All jitter values are based on a bit-error ratio of $1e^{-12}$.
4. PLL frequency at 1.5625 GHz and OUTDIV = 1.
5. PLL frequency at 2.5 GHz and OUTDIV = 2.
6. PLL frequency at 2.5 GHz and OUTDIV = 4.

Table 35: **GTH Transceiver User Clock Switching Characteristics** (1)

Symbol	Description	Conditions	Speed Grade			Units
			-3	-2	-1	
F_{TXOUT}	TXUSERCLKOUT maximum frequency		350	350	323	MHz
F_{RXOUT}	RXUSERCLKOUT maximum frequency		350	350	323	MHz
F_{TXIN}	TXUSERCLKIN maximum frequency	16-bit data path	350	350	323	MHz
		20-bit data path	280	280	258	MHz
		32-bit data path	350	350	323	MHz
		40-bit data path	280	280	258	MHz
		64-bit data path	175	175	162	MHz
		80-bit data path	140	140	129	MHz
		64B/66B-bit data path	170	170	157	MHz
F_{RXIN}	RXUSERCLKIN maximum frequency	16-bit data path	350	350	323	MHz
		20-bit data path	280	280	258	MHz
		32-bit data path	350	350	323	MHz
		40-bit data path	280	280	258	MHz
		64-bit data path	175	175	162	MHz
		80-bit data path	140	140	129	MHz
		64B/66B-bit data path	170	170	157	MHz

Notes:

1. Clocking must be implemented as described in UG371:*Virtex-6 FPGA GTH Transceivers User Guide*.

Table 36: **GTH Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
T_{RTX}	TX Rise time	20%–80%	–	50(3)	–	ps
T_{FTX}	TX Fall time	80%–20%	–	50(3)	–	ps
T_{LLSKEW}	TX lane-to-lane skew	within one GTH Quad	–	–	300	ps
Transmitter Output Jitter(1)(2)						
$TJ_{11.18}$	Total Jitter	11.181 Gb/s	–	–	0.280	UI
$DJ_{11.18}$	Deterministic Jitter		–	–	0.170	UI
$TJ_{10.3125}$	Total Jitter	10.3125 Gb/s	–	–	0.280	UI
$DJ_{10.3125}$	Deterministic Jitter		–	–	0.170	UI
$TJ_{9.953}$	Total Jitter	9.953 Gb/s	–	–	0.280	UI
$DJ_{9.953}$	Deterministic Jitter		–	–	0.170	UI
$TJ_{2.667}$	Total Jitter	2.667 Gb/s	–	–	0.110	UI
$DJ_{2.667}$	Deterministic Jitter		–	–	0.060	UI
$TJ_{2.488}$	Total Jitter	2.488 Gb/s	–	–	0.110	UI
$DJ_{2.488}$	Deterministic Jitter		–	–	0.060	UI

Notes:

1. These values are NOT intended for protocol specific compliance determinations.
2. All jitter values are based on a bit-error ratio of $1e^{-12}$.
3. Rise and fall times are specified at the transmitter package balls.

Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Virtex-6 devices. The numbers reported here are worst-case values; they have all been fully characterized. These values are subject to the same guidelines as the Switching Characteristics, page 26.

Table 41: **Interface Performances**

Description	Speed Grade			
	-3	**-2**	**-1**	**-1L**
Networking Applications				
SDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 8)	710 Mb/s	710 Mb/s	650 Mb/s	585 Mb/s
DDR LVDS transmitter (using OSERDES; DATA_WIDTH = 4 to 10)	1.4 Gb/s	1.3 Gb/s	1.25 Gb/s	1.1 Gb/s
SDR LVDS receiver (SFI-4.1)(1)	710 Mb/s	710 Mb/s	650 Mb/s	585 Mb/s
DDR LVDS receiver (SPI-4.2)(1)	1.4 Gb/s	1.3 Gb/s	1.1 Gb/s	0.9 Gb/s
Maximum Physical Interface (PHY) Rate for Memory Interfaces(2)(3)(4)				
DDR2	800 Mb/s	800 Mb/s	800 Mb/s	606 Mb/s
DDR3	1066 Mb/s	1066 Mb/s	800 Mb/s	800 Mb/s
QDR II + SRAM	400 MHz	350 MHz	300 MHz	–
RLDRAM II	500 MHz	400 MHz	350 MHz	–

Notes:

1. LVDS receivers are typically bounded with certain applications where specific DPA algorithms dominate deterministic performance.
2. Verified on Xilinx memory characterization platforms designed according to the guidelines in UG: *Virtex-6 FPGA Memory Interface Solutions User Guide*.
3. Consult DS186: *Virtex-6 FPGA Memory Interface Solutions Data Sheet* for performance and feature information on memory interface cores (controller plus PHY).
4. Memory Interface data rates have not been tested over the junction temperature operating range for military (M) temperature devices. Customers are responsible for specifying and testing their specific M temperature grade memory implementation.

Table 44: **IOB Switching Characteristics for the Commercial (XC) Virtex-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-2	-1	-1L	-3	-2	-1	-1L	-3	-2	-1	-1L	
LVCMOS25, Fast, 24 mA	0.51	0.57	0.66	0.70	1.66	1.79	1.99	1.96	1.66	1.79	1.99	1.96	ns
LVCMOS18, Slow, 2 mA	0.55	0.61	0.71	0.73	4.21	4.47	4.87	4.30	4.21	4.47	4.87	4.30	ns
LVCMOS18, Slow, 4 mA	0.55	0.61	0.71	0.73	2.79	2.96	3.21	2.94	2.79	2.96	3.21	2.94	ns
LVCMOS18, Slow, 6 mA	0.55	0.61	0.71	0.73	2.30	2.43	2.64	2.47	2.30	2.43	2.64	2.47	ns
LVCMOS18, Slow, 8 mA	0.55	0.61	0.71	0.73	2.01	2.11	2.27	2.24	2.01	2.11	2.27	2.24	ns
LVCMOS18, Slow, 12 mA	0.55	0.61	0.71	0.73	1.88	1.99	2.15	2.10	1.88	1.99	2.15	2.10	ns
LVCMOS18, Slow, 16 mA	0.55	0.61	0.71	0.73	1.84	1.95	2.11	2.04	1.84	1.95	2.11	2.04	ns
LVCMOS18, Fast, 2 mA	0.55	0.61	0.71	0.73	4.00	4.23	4.57	4.08	4.00	4.23	4.57	4.08	ns
LVCMOS18, Fast, 4 mA	0.55	0.61	0.71	0.73	2.62	2.76	2.97	2.74	2.62	2.76	2.97	2.74	ns
LVCMOS18, Fast, 6 mA	0.55	0.61	0.71	0.73	2.15	2.28	2.46	2.32	2.15	2.28	2.46	2.32	ns
LVCMOS18, Fast, 8 mA	0.55	0.61	0.71	0.73	1.90	1.99	2.13	2.14	1.90	1.99	2.13	2.14	ns
LVCMOS18, Fast, 12 mA	0.55	0.61	0.71	0.73	1.69	1.80	1.97	1.88	1.69	1.80	1.97	1.88	ns
LVCMOS18, Fast, 16 mA	0.55	0.61	0.71	0.73	1.63	1.74	1.91	1.88	1.63	1.74	1.91	1.88	ns
LVCMOS15, Slow, 2 mA	0.64	0.73	0.85	0.85	3.43	3.77	4.29	3.91	3.43	3.77	4.29	3.91	ns
LVCMOS15, Slow, 4 mA	0.64	0.73	0.85	0.85	2.58	2.79	3.10	2.93	2.58	2.79	3.10	2.93	ns
LVCMOS15, Slow, 6 mA	0.64	0.73	0.85	0.85	2.08	2.32	2.68	2.50	2.08	2.32	2.68	2.50	ns
LVCMOS15, Slow, 8 mA	0.64	0.73	0.85	0.85	1.81	1.98	2.23	2.24	1.81	1.98	2.23	2.24	ns
LVCMOS15, Slow, 12 mA	0.64	0.73	0.85	0.85	1.76	1.91	2.13	2.07	1.76	1.91	2.13	2.07	ns
LVCMOS15, Slow, 16 mA	0.64	0.73	0.85	0.85	1.69	1.83	2.04	1.98	1.69	1.83	2.04	1.98	ns
LVCMOS15, Fast, 2 mA	0.64	0.73	0.85	0.85	3.44	3.77	4.28	3.91	3.44	3.77	4.28	3.91	ns
LVCMOS15, Fast, 4 mA	0.64	0.73	0.85	0.85	2.37	2.53	2.78	2.66	2.37	2.53	2.78	2.66	ns
LVCMOS15, Fast, 6 mA	0.64	0.73	0.85	0.85	1.80	2.05	2.42	2.16	1.80	2.05	2.42	2.16	ns
LVCMOS15, Fast, 8 mA	0.64	0.73	0.85	0.85	1.76	1.90	2.11	2.04	1.76	1.90	2.11	2.04	ns
LVCMOS15, Fast, 12 mA	0.64	0.73	0.85	0.85	1.64	1.77	1.97	1.90	1.64	1.77	1.97	1.90	ns
LVCMOS15, Fast, 16 mA	0.64	0.73	0.85	0.85	1.62	1.76	1.96	1.92	1.62	1.76	1.96	1.92	ns
LVCMOS12, Slow, 2 mA	0.72	0.81	0.93	0.95	3.14	3.39	3.75	3.54	3.14	3.39	3.75	3.54	ns
LVCMOS12, Slow, 4 mA	0.72	0.81	0.93	0.95	2.43	2.63	2.93	2.79	2.43	2.63	2.93	2.79	ns
LVCMOS12, Slow, 6 mA	0.72	0.81	0.93	0.95	1.92	2.11	2.41	2.26	1.92	2.11	2.41	2.26	ns
LVCMOS12, Slow, 8 mA	0.72	0.81	0.93	0.95	1.87	2.02	2.25	2.17	1.87	2.02	2.25	2.17	ns
LVCMOS12, Fast, 2 mA	0.72	0.81	0.93	0.95	2.71	2.98	3.39	3.11	2.71	2.98	3.39	3.11	ns
LVCMOS12, Fast, 4 mA	0.72	0.81	0.93	0.95	1.93	2.16	2.51	2.31	1.93	2.16	2.51	2.31	ns
LVCMOS12, Fast, 6 mA	0.72	0.81	0.93	0.95	1.75	1.89	2.11	2.05	1.75	1.89	2.11	2.05	ns
LVCMOS12, Fast, 8 mA	0.72	0.81	0.93	0.95	1.69	1.82	2.02	1.98	1.69	1.82	2.02	1.98	ns
LVDCI_25	0.51	0.57	0.66	0.70	2.05	2.14	2.26	2.26	2.05	2.14	2.26	2.26	ns
LVDCI_18	0.55	0.61	0.71	0.73	2.07	2.23	2.47	2.38	2.07	2.23	2.47	2.38	ns
LVDCI_15	0.64	0.73	0.85	0.85	1.85	2.01	2.24	2.18	1.85	2.01	2.24	2.18	ns

Table 44: **IOB Switching Characteristics for the Commercial (XC) Virtex-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}				T_{IOOP}				T_{IOTP}				Units
	Speed Grade				Speed Grade				Speed Grade				
	-3	-2	-1	-1L	-3	-2	-1	-1L	-3	-2	-1	-1L	
LVDCI_DV2_25	0.51	0.57	0.66	0.70	1.71	1.83	2.01	2.00	1.71	1.83	2.01	2.00	ns
LVDCI_DV2_18	0.55	0.61	0.71	0.73	1.69	1.81	2.00	1.98	1.69	1.81	2.00	1.98	ns
LVDCI_DV2_15	0.64	0.73	0.85	0.85	1.68	1.77	1.91	1.98	1.68	1.77	1.91	1.98	ns
LVPECL_25	0.85	0.94	1.09	1.08	1.38	1.49	1.65	1.64	1.38	1.49	1.65	1.64	ns
HSTL_I_12	0.81	0.91	1.06	1.06	1.48	1.60	1.78	1.74	1.48	1.60	1.78	1.74	ns
HSTL_I_DCI	0.81	0.91	1.06	1.06	1.40	1.50	1.66	1.64	1.40	1.50	1.66	1.64	ns
HSTL_II_DCI	0.81	0.91	1.06	1.06	1.37	1.49	1.68	1.66	1.37	1.49	1.68	1.66	ns
HSTL_II_T_DCI	0.81	0.91	1.06	1.06	1.40	1.50	1.66	1.64	1.40	1.50	1.66	1.64	ns
HSTL_III_DCI	0.81	0.91	1.06	1.06	1.34	1.45	1.62	1.61	1.34	1.45	1.62	1.61	ns
HSTL_I_DCI_18	0.81	0.91	1.06	1.06	1.42	1.53	1.68	1.66	1.42	1.53	1.68	1.66	ns
HSTL_II_DCI_18	0.81	0.91	1.06	1.06	1.36	1.46	1.62	1.59	1.36	1.46	1.62	1.59	ns
HSTL_II _T_DCI_18	0.81	0.91	1.06	1.06	1.42	1.53	1.68	1.66	1.42	1.53	1.68	1.66	ns
HSTL_III_DCI_18	0.81	0.91	1.06	1.06	1.43	1.54	1.69	1.67	1.43	1.54	1.69	1.67	ns
DIFF_HSTL_I_18	0.85	0.94	1.09	1.08	1.47	1.58	1.75	1.72	1.47	1.58	1.75	1.72	ns
DIFF_HSTL_I_DCI_18	0.85	0.94	1.09	1.08	1.42	1.53	1.68	1.66	1.42	1.53	1.68	1.66	ns
DIFF_HSTL_I	0.85	0.94	1.09	1.08	1.45	1.56	1.73	1.71	1.45	1.56	1.73	1.71	ns
DIFF_HSTL_I_DCI	0.85	0.94	1.09	1.08	1.40	1.50	1.66	1.64	1.40	1.50	1.66	1.64	ns
DIFF_HSTL_II_18	0.85	0.94	1.09	1.08	1.50	1.62	1.81	1.78	1.50	1.62	1.81	1.78	ns
DIFF_HSTL_II_DCI_18	0.85	0.94	1.09	1.08	1.36	1.46	1.62	1.59	1.36	1.46	1.62	1.59	ns
DIFF_HSTL_II _T_DCI_18	0.85	0.94	1.09	1.08	1.42	1.53	1.68	1.66	1.42	1.53	1.68	1.66	ns
DIFF_HSTL_II	0.85	0.94	1.09	1.08	1.44	1.56	1.74	1.72	1.44	1.56	1.74	1.72	ns
DIFF_HSTL_II_DCI	0.85	0.94	1.09	1.08	1.37	1.49	1.68	1.66	1.37	1.49	1.68	1.66	ns
SSTL2_I_DCI	0.81	0.91	1.06	1.06	1.42	1.53	1.70	1.68	1.42	1.53	1.70	1.68	ns
SSTL2_II_DCI	0.81	0.91	1.06	1.06	1.39	1.50	1.67	1.69	1.39	1.50	1.67	1.69	ns
SSTL2_II_T_DCI	0.81	0.91	1.06	1.06	1.42	1.53	1.70	1.68	1.42	1.53	1.70	1.68	ns
SSTL18_I	0.81	0.91	1.06	1.06	1.47	1.58	1.75	1.73	1.47	1.58	1.75	1.73	ns
SSTL18_II	0.81	0.91	1.06	1.06	1.39	1.50	1.67	1.66	1.39	1.50	1.67	1.66	ns
SSTL18_I_DCI	0.81	0.91	1.06	1.06	1.40	1.51	1.67	1.65	1.40	1.51	1.67	1.65	ns
SSTL18_II_DCI	0.81	0.91	1.06	1.06	1.36	1.47	1.63	1.62	1.36	1.47	1.63	1.62	ns
SSTL18_II_T_DCI	0.81	0.91	1.06	1.06	1.40	1.51	1.67	1.65	1.40	1.51	1.67	1.65	ns
SSTL15_T_DCI	0.81	0.91	1.06	1.06	1.41	1.52	1.68	1.66	1.41	1.52	1.68	1.66	ns
SSTL15_DCI	0.81	0.91	1.06	1.06	1.41	1.52	1.68	1.66	1.41	1.52	1.68	1.66	ns
DIFF_SSTL2_I	0.85	0.94	1.09	1.08	1.49	1.60	1.77	1.74	1.49	1.60	1.77	1.74	ns
DIFF_SSTL2_I_DCI	0.85	0.94	1.09	1.08	1.42	1.53	1.70	1.68	1.42	1.53	1.70	1.68	ns
DIFF_SSTL2_II	0.85	0.94	1.09	1.08	1.42	1.54	1.72	1.71	1.42	1.54	1.72	1.71	ns
DIFF_SSTL2_II_DCI	0.85	0.94	1.09	1.08	1.39	1.50	1.67	1.69	1.39	1.50	1.67	1.69	ns
DIFF_SSTL2_II_T_DCI	0.85	0.94	1.09	1.08	1.42	1.53	1.70	1.68	1.42	1.53	1.70	1.68	ns

Table 45: **IOB Switching Characteristics for the Defense-grade (XQ) Virtex-6 Devices *(Cont'd)***

I/O Standard	T_{IOPI}			T_{IOOP}			T_{IOTP}			Units
	Speed Grade			Speed Grade			Speed Grade			
	-2	-1	-1L	-2	-1	-1L	-2	-1	-1L	
LVCMOS25, Fast, 16 mA	0.57	0.66	0.70	1.92	2.15	2.08	1.92	2.15	2.08	ns
LVCMOS25, Fast, 24 mA	0.57	0.66	0.70	1.79	2.15	1.96	1.79	2.15	1.96	ns
LVCMOS18, Slow, 2 mA	0.61	0.71	0.73	4.47	4.87	4.30	4.47	4.87	4.30	ns
LVCMOS18, Slow, 4 mA	0.61	0.71	0.73	2.96	3.21	2.94	2.96	3.21	2.94	ns
LVCMOS18, Slow, 6 mA	0.61	0.71	0.73	2.43	2.64	2.47	2.43	2.64	2.47	ns
LVCMOS18, Slow, 8 mA	0.61	0.71	0.73	2.11	2.41	2.24	2.11	2.41	2.24	ns
LVCMOS18, Slow, 12 mA	0.61	0.71	0.73	1.99	2.30	2.10	1.99	2.30	2.10	ns
LVCMOS18, Slow, 16 mA	0.61	0.71	0.73	1.95	2.30	2.04	1.95	2.30	2.04	ns
LVCMOS18, Fast, 2 mA	0.61	0.71	0.73	4.23	4.57	4.08	4.23	4.57	4.08	ns
LVCMOS18, Fast, 4 mA	0.61	0.71	0.73	2.76	2.97	2.74	2.76	2.97	2.74	ns
LVCMOS18, Fast, 6 mA	0.61	0.71	0.73	2.28	2.46	2.32	2.28	2.46	2.32	ns
LVCMOS18, Fast, 8 mA	0.61	0.71	0.73	1.99	2.34	2.14	1.99	2.34	2.14	ns
LVCMOS18, Fast, 12 mA	0.61	0.71	0.73	1.80	2.19	1.88	1.80	2.19	1.88	ns
LVCMOS18, Fast, 16 mA	0.61	0.71	0.73	1.74	2.18	1.88	1.74	2.18	1.88	ns
LVCMOS15, Slow, 2 mA	0.73	0.85	0.85	3.77	4.29	3.91	3.77	4.29	3.91	ns
LVCMOS15, Slow, 4 mA	0.73	0.85	0.85	2.79	3.10	2.93	2.79	3.10	2.93	ns
LVCMOS15, Slow, 6 mA	0.73	0.85	0.85	2.32	2.68	2.50	2.32	2.68	2.50	ns
LVCMOS15, Slow, 8 mA	0.73	0.85	0.85	1.98	2.29	2.24	1.98	2.29	2.24	ns
LVCMOS15, Slow, 12 mA	0.73	0.85	0.85	1.91	2.23	2.07	1.91	2.23	2.07	ns
LVCMOS15, Slow, 16 mA	0.73	0.85	0.85	1.83	2.23	1.98	1.83	2.23	1.98	ns
LVCMOS15, Fast, 2 mA	0.73	0.85	0.85	3.77	4.28	3.91	3.77	4.28	3.91	ns
LVCMOS15, Fast, 4 mA	0.73	0.85	0.85	2.53	2.78	2.66	2.53	2.78	2.66	ns
LVCMOS15, Fast, 6 mA	0.73	0.85	0.85	2.05	2.42	2.16	2.05	2.42	2.16	ns
LVCMOS15, Fast, 8 mA	0.73	0.85	0.85	1.90	2.20	2.04	1.90	2.20	2.04	ns
LVCMOS15, Fast, 12 mA	0.73	0.85	0.85	1.77	2.11	1.90	1.77	2.11	1.90	ns
LVCMOS15, Fast, 16 mA	0.73	0.85	0.85	1.76	2.11	1.92	1.76	2.11	1.92	ns
LVCMOS12, Slow, 2 mA	0.81	0.93	0.95	3.39	3.75	3.54	3.39	3.75	3.54	ns
LVCMOS12, Slow, 4 mA	0.81	0.93	0.95	2.63	2.93	2.79	2.63	2.93	2.79	ns
LVCMOS12, Slow, 6 mA	0.81	0.93	0.95	2.11	2.67	2.26	2.11	2.67	2.26	ns
LVCMOS12, Slow, 8 mA	0.81	0.93	0.95	2.02	2.25	2.17	2.02	2.25	2.17	ns
LVCMOS12, Fast, 2 mA	0.81	0.93	0.95	2.98	3.39	3.11	2.98	3.39	3.11	ns
LVCMOS12, Fast, 4 mA	0.81	0.93	0.95	2.16	2.70	2.31	2.16	2.70	2.31	ns
LVCMOS12, Fast, 6 mA	0.81	0.93	0.95	1.89	2.34	2.05	1.89	2.34	2.05	ns
LVCMOS12, Fast, 8 mA	0.81	0.93	0.95	1.82	2.10	1.98	1.82	2.10	1.98	ns
LVDCI_25	0.57	0.70	0.70	2.14	2.82	2.26	2.14	2.82	2.26	ns
LVDCI_18	0.61	0.71	0.73	2.23	2.78	2.38	2.23	2.78	2.38	ns
LVDCI_15	0.73	0.85	0.85	2.01	2.75	2.18	2.01	2.75	2.18	ns
LVDCI_DV2_25	0.57	0.70	0.70	1.83	2.37	2.00	1.83	2.37	2.00	ns

I/O Standard Adjustment Measurement Methodology

Input Delay Measurements

Table 47 shows the test setup parameters used for measuring input delay.

Table 47: **Input Delay Measurement Methodology**

Description	I/O Standard Attribute	V_L (1)(2)	V_H (1)(2)	V_{MEAS} (1)(4)(5)	V_{REF} (1)(3)(5)
LVCMOS, 2.5V	LVCMOS25	0	2.5	1.25	–
LVCMOS, 1.8V	LVCMOS18	0	1.8	0.9	–
LVCMOS, 1.5V	LVCMOS15	0	1.5	0.75	–
HSTL (High-Speed Transceiver Logic), Class I & II	HSTL_I, HSTL_II	V_{REF} – 0.5	V_{REF} + 0.5	V_{REF}	0.75
HSTL, Class III	HSTL_III	V_{REF} – 0.5	V_{REF} + 0.5	V_{REF}	0.90
HSTL, Class I & II, 1.8V	HSTL_I_18, HSTL_II_18	V_{REF} – 0.5	V_{REF} + 0.5	V_{REF}	0.90
HSTL, Class III 1.8V	HSTL_III_18	V_{REF} – 0.5	V_{REF} + 0.5	V_{REF}	1.08
SSTL (Stub Terminated Transceiver Logic), Class I & II, 3.3V	SSTL3_I, SSTL3_II	V_{REF} – 1.00	V_{REF} + 1.00	V_{REF}	1.5
SSTL, Class I & II, 2.5V	SSTL2_I, SSTL2_II	V_{REF} – 0.75	V_{REF} + 0.75	V_{REF}	1.25
SSTL, Class I & II, 1.8V	SSTL18_I, SSTL18_II	V_{REF} – 0.5	V_{REF} + 0.5	V_{REF}	0.90
LVDS (Low-Voltage Differential Signaling), 2.5V	LVDS_25	1.2 – 0.125	1.2 + 0.125	0(6)	–
LVDSEXT (LVDS Extended Mode), 2.5V	LVDSEXT_25	1.2 – 0.125	1.2 + 0.125	0(6)	–
HT (HyperTransport), 2.5V	LDT_25	0.6 – 0.125	0.6 + 0.125	0(6)	–

Notes:

1. The input delay measurement methodology parameters for LVDCI are the same for LVCMOS standards of the same voltage. Input delay measurement methodology parameters for HSLVDCI are the same as for HSTL_II standards of the same voltage. Parameters for all other DCI standards are the same for the corresponding non-DCI standards.
2. Input waveform switches between V_L and V_H.
3. Measurements are made at typical, minimum, and maximum V_{REF} values. Reported delays reflect worst case of these measurements. V_{REF} values listed are typical.
4. Input voltage level from which measurement starts.
5. This is an input voltage reference that bears no relation to the V_{REF} / V_{MEAS} parameters found in IBIS models and/or noted in Figure 6.
6. The value given is the differential input voltage.

Output Delay Measurements

Output delays are measured using a Tektronix P6245 TDS500/600 probe (< 1 pF) across approximately 4" of FR4 microstrip trace. Standard termination was used for all testing. The propagation delay of the 4" trace is characterized separately and subtracted from the final measurement, and is therefore not included in the generalized test setups shown in Figure 6 and Figure 7.

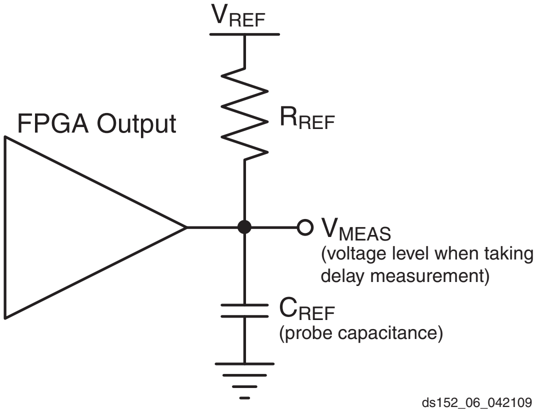

Figure 6: **Single Ended Test Setup**

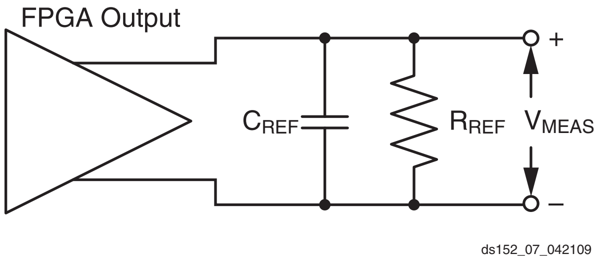

Figure 7: **Differential Test Setup**

Measurements and test conditions are reflected in the IBIS models except where the IBIS format precludes it. Parameters V_{REF}, R_{REF}, C_{REF}, and V_{MEAS} fully describe the test conditions for each I/O standard. The most accurate prediction of propagation delay in any given application can be obtained through IBIS simulation, using the following method:

1. Simulate the output driver of choice into the generalized test setup, using values from Table 48.
2. Record the time to V_{MEAS}.
3. Simulate the output driver of choice into the actual PCB trace and load, using the appropriate IBIS model or capacitance value to represent the load.
4. Record the time to V_{MEAS}.
5. Compare the results of steps 2 and 4. The increase or decrease in delay yields the actual propagation delay of the PCB trace.

Table 48: **Output Delay Measurement Methodology**

Description	I/O Standard Attribute	R_{REF} (Ω)	C_{REF}(1) (pF)	V_{MEAS} (V)	V_{REF} (V)
LVCMOS, 2.5V	LVCMOS25	1M	0	1.25	0
LVCMOS, 1.8V	LVCMOS18	1M	0	0.9	0
LVCMOS, 1.5V	LVCMOS15	1M	0	0.75	0
LVCMOS, 1.2V	LVCMOS12	1M	0	0.75	0
HSTL (High-Speed Transceiver Logic), Class I	HSTL_I	50	0	V_{REF}	0.75
HSTL, Class II	HSTL_II	25	0	V_{REF}	0.75
HSTL, Class III	HSTL_III	50	0	0.9	1.5
HSTL, Class I, 1.8V	HSTL_I_18	50	0	V_{REF}	0.9
HSTL, Class II, 1.8V	HSTL_II_18	25	0	V_{REF}	0.9
HSTL, Class III, 1.8V	HSTL_III_18	50	0	1.1	1.8
SSTL (Stub Series Terminated Logic), Class I, 1.8V	SSTL18_I	50	0	V_{REF}	0.9
SSTL, Class II, 1.8V	SSTL18_II	25	0	V_{REF}	0.9
SSTL, Class I, 2.5V	SSTL2_I	50	0	V_{REF}	1.25
SSTL, Class II, 2.5V	SSTL2_II	25	0	V_{REF}	1.25
LVDS (Low-Voltage Differential Signaling), 2.5V	LVDS_25	100	0	0(2)	1.2
LVDSEXT (LVDS Extended Mode), 2.5V	LVDS_25	100	0	0(2)	1.2
BLVDS (Bus LVDS), 2.5V	BLVDS_25	100	0	0(2)	0

Table 50: **OLOGIC Switching Characteristics**

Symbol	Description	Speed Grade					Units
		-3	-2	-1 (XC)	-1 (XQ)	-1L	
Setup/Hold							
T_{ODCK}/T_{OCKD}	D1/D2 pins Setup/Hold with respect to CLK	0.45/–0.08	0.50/–0.08	0.54/–0.08	0.54/–0.08	0.69/–0.11	ns
T_{OOCECK}/T_{OCKOCE}	OCE pin Setup/Hold with respect to CLK	0.17/–0.03	0.20/–0.03	0.22/–0.03	0.27/–0.05	0.27/–0.04	ns
T_{OSRCK}/T_{OCKSR}	SR pin Setup/Hold with respect to CLK	0.59/–0.24	0.62/–0.24	0.54/–0.08	0.54/–0.08	0.79/–0.35	ns
T_{OTCK}/T_{OCKT}	T1/T2 pins Setup/Hold with respect to CLK	0.44/–0.07	0.51/–0.07	0.56/–0.07	0.60/–0.10	0.68/–0.13	ns
T_{OTCECK}/T_{OCKTCE}	TCE pin Setup/Hold with respect to CLK	0.15/–0.04	0.19/–0.04	0.21/–0.04	0.27/–0.05	0.29/–0.05	ns
Combinatorial							
T_{DOQ}	D1 to OQ out or T1 to TQ out	0.78	0.87	1.01	1.01	1.15	ns
Sequential Delays							
T_{OCKQ}	CLK to OQ/TQ out	0.54	0.61	0.71	0.71	0.80	ns
T_{RQ}	SR pin to OQ/TQ out	0.80	0.90	1.05	1.05	1.19	ns
T_{GSRQ}	Global Set/Reset to Q outputs	7.60	7.60	10.51	10.51	10.51	ns
Set/Reset							
T_{RPW}	Minimum Pulse Width, SR inputs	0.78	0.95	1.20	1.20	1.30	ns, Min

Input/Output Delay Switching Characteristics

Table 53: **Input/Output Delay Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
IDELAYCTRL						
T_{DLYCCO_RDY}	Reset to Ready for IDELAYCTRL	3.00	3.00	3.00	3.25	µs
$F_{IDELAYCTRL\_REF}$	REFCLK frequency = 200.0(1)	200	200	200	200	MHz
	REFCLK frequency = 300.0(1)	300	300	–	–	MHz
IDELAYCTRL_REF_PRECISION	REFCLK precision	±10	±10	±10	±10	MHz
$T_{IDELAYCTRL\_RPW}$	Minimum Reset pulse width	50.00	50.00	50.00	52.50	ns
IODELAY						
$T_{IDELAYRESOLUTION}$	IODELAY Chain Delay Resolution	1/(32 x 2 x F_{REF})				ps
$T_{IDELAYPAT\_JIT}$	Pattern dependent period jitter in delay chain for clock pattern.(2)	0	0	0	0	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23).(3)	±5	±5	±5	±5	ps per tap
	Pattern dependent period jitter in delay chain for random data pattern (PRBS 23).(4)	±9	±9	±9	±9	ps per tap
$T_{IODELAY\_CLK\_MAX}$	Maximum frequency of CLK input to IODELAY	500.00	420.00	300.00	300.00	MHz
T_{IODCCK_CE} / T_{IODCKC_CE}	CE pin Setup/Hold with respect to CK	0.45/ –0.09	0.53/ –0.09	0.65/ –0.09	0.84/ –0.14	ns
T_{IODCK_INC}/ T_{IODCKC_INC}	INC pin Setup/Hold with respect to CK	0.23/ –0.02	0.27/ –0.01	0.31/ 0.00	0.27/ –0.04	ns
T_{IODCCK_RST}/ T_{IODCKC_RST}	RST pin Setup/Hold with respect to CK	0.57/ –0.08	0.62/ –0.08	0.69/ –0.08	0.74/ –0.13	ns
T_{IODDO_T}	TSCONTROL delay to MUXE/MUXF switching and through IODELAY	Note 5	Note 5	Note 5	Note 5	ps
$T_{IODDO\_IDATAIN}$	Propagation delay through IODELAY	Note 5	Note 5	Note 5	Note 5	ps
$T_{IODDO\_ODATAIN}$	Propagation delay through IODELAY	Note 5	Note 5	Note 5	Note 5	ps

Notes:

1. Average Tap Delay at 200 MHz = 78 ps, at 300 MHz = 52 ps.
2. When HIGH_PERFORMANCE mode is set to TRUE or FALSE.
3. When HIGH_PERFORMANCE mode is set to TRUE
4. When HIGH_PERFORMANCE mode is set to FALSE.
5. Delay depends on IODELAY tap setting. See TRACE report for actual values.

CLB Switching Characteristics

Table 54: **CLB Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Combinatorial Delays						
T_{ILO}	An – Dn LUT address to A	0.06	0.07	0.07	0.09	ns, Max
	An – Dn LUT address to AMUX/CMUX	0.18	0.20	0.22	0.25	ns, Max
	An – Dn LUT address to BMUX_A	0.28	0.31	0.36	0.40	ns, Max

CLB Distributed RAM Switching Characteristics (SLICEM Only)

Table 55: **CLB Distributed RAM Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Sequential Delays						
T_{SHCKO}	Clock to A – B outputs	0.92	1.10	1.36	1.49	ns, Max
T_{SHCKO_1}	Clock to AMUX – BMUX outputs	1.19	1.40	1.71	1.87	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{DS}/T_{DH}	A – D inputs to CLK	0.62/0.18	0.72/0.20	0.88/0.22	0.98/0.23	ns, Min
T_{AS}/T_{AH}	Address An inputs to clock	0.19/0.52	0.22/0.59	0.27/0.66	0.30/0.75	ns, Min
T_{WS}/T_{WH}	WE input to clock	0.27/0.00	0.32/0.00	0.40/0.00	0.47/–0.03	ns, Min
T_{CECK}/T_{CKCE}	CE input to CLK	0.28/–0.01	0.34/–0.01	0.41/–0.01	0.48/–0.05	ns, Min
Clock CLK						
T_{MPW}	Minimum pulse width	0.70	0.82	1.00	1.04	ns, Min
T_{MCP}	Minimum clock period	1.40	1.64	2.00	2.08	ns, Min

Notes:

1. A Zero “0” Hold Time listing indicates no hold time or a negative hold time. Negative values cannot be guaranteed “best-case”, but if a “0” is listed, there is no positive hold time.
2. T_{SHCKO} also represents the CLK to XMUX output. Refer to TRACE report for the CLK to XMUX path.

CLB Shift Register Switching Characteristics (SLICEM Only)

Table 56: **CLB Shift Register Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Sequential Delays						
T_{REG}	Clock to A – D outputs	1.11	1.30	1.58	1.74	ns, Max
T_{REG_MUX}	Clock to AMUX – DMUX output	1.37	1.60	1.93	2.12	ns, Max
T_{REG_M31}	Clock to DMUX output via M31 output	1.08	1.27	1.55	1.74	ns, Max
Setup and Hold Times Before/After Clock CLK						
T_{WS}/T_{WH}	WE input	0.05/0.00	0.07/0.00	0.09/0.00	0.11/0.03	ns, Min
T_{CECK}/T_{CKCE}	CE input to CLK	0.06/–0.01	0.08/–0.01	0.10/–0.01	0.12/0.02	ns, Min
T_{DS}/T_{DH}	A – D inputs to CLK	0.64/0.18	0.76/0.21	0.94/0.24	1.07/0.23	ns, Min
Clock CLK						
T_{MPW}	Minimum pulse width	0.60	0.70	0.85	0.89	ns, Min

Notes:

1. A Zero “0” Hold Time listing indicates no hold time or a negative hold time. Negative values cannot be guaranteed “best-case”, but if a “0” is listed, there is no positive hold time.

Table 58: **DSP48E1 Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade					Units
		-3	-2	-1 (XC)	-1 (XQ)	-1L	
Maximum Frequency							
F_{MAX}	With all registers used	600	540	450	450	410	MHz
F_{MAX_PATDET}	With pattern detector	551	483	408	408	356	MHz
$F_{MAX\_MULT\_NOMREG}$	Two register multiply without MREG	356	311	262	262	224	MHz
$F_{MAX\_MULT\_NOMREG\_PATDET}$	Two register multiply without MREG with pattern detect	327	286	241	241	211	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG}$	Without ADREG	398	347	292	292	254	MHz
$F_{MAX\_PREADD\_MULT\_NOADREG\_PATDET}$	Without ADREG with pattern detect	398	347	292	292	254	MHz
$F_{MAX\_NOPIPELINEREG}$	Without pipeline registers (MREG, ADREG)	266	233	196	196	171	MHz
$F_{MAX\_NOPIPELINEREG\_PATDET}$	Without pipeline registers (MREG, ADREG) with pattern detect	250	219	184	184	160	MHz

Configuration Switching Characteristics

Table 59: **Configuration Switching Characteristics**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Power-up Timing Characteristics						
T_{PL}(1)	Program Latency	5	5	5	5	ms, Max
T_{POR}(1)	Power-on-Reset	15/55	15/55	15/55	15/60	ms, Min/Max
T_{ICCK}	CCLK (output) delay	400	400	400	400	ns, Min
$T_{PROGRAM}$	Program Pulse Width	250	250	250	250	ns, Min
Master/Slave Serial Mode Programming Switching						
T_{DCCK}/T_{CCKD}	DIN Setup/Hold, slave mode	4.0/0.0	4.0/0.0	4.0/0.0	4.5/0.0	ns, Min
T_{DSCCK}/T_{SCCKD}	DIN Setup/Hold, master mode	4.0/0.0	4.0/0.0	4.0/0.0	5.0/0.0	ns, Min
T_{CCO}	DOUT at 2.5V	6	6	6	7	ns, Max
	DOUT at 1.8V	6	6	6	7	ns, Max
F_{MCCK}	Maximum CCLK frequency, serial modes	105	105	105	70	MHz, Max
$F_{MCCKTOL}$	Frequency Tolerance, master mode with respect to nominal CCLK.	55	55	55	60	%
F_{MSCCK}	Slave mode external CCLK	100	100	100	100	MHz
SelectMAP Mode Programming Switching						
T_{SMDCCK}/T_{SMCCKD}	SelectMAP Data Setup/Hold	4.0/0.0	4.0/0.0	4.0/0.0	5.5/0.0	ns, Min
$T_{SMCSCCK}/T_{SMCCKCS}$	CSI_B Setup/Hold	4.0/0.0	4.0/0.0	4.0/0.0	5.5/0.0	ns, Min
T_{SMCCKW}/T_{SMWCCK}	RDWR_B Setup/Hold	10.0/0.0	10.0/0.0	10.0/0.0	16.0/0.0	ns, Min
$T_{SMCKCSO}$	CSO_B clock to out (330 Ω pull-up resistor required)	6	6	6	7	ns, Max
T_{SMCO}	CCLK to DATA out in readback at 2.5V	6	6	6	7	ns, Max
	CCLK to DATA out in readback at 1.8V	6	6	6	7	ns, Max

Table 59: **Configuration Switching Characteristics *(Cont'd)***

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
$T_{MMCMDCK\_DI}$/ $T_{MMCMCKD\_DI}$	DI Setup/Hold	1.25/ 0.00	1.40/ 0.00	1.63/ 0.00	1.64/ 0.00	ns
$T_{MMCMDCK\_DEN}$/ $T_{MMCMCKD\_DEN}$	DEN Setup/Hold time	1.25/ 0.00	1.40/ 0.00	1.63/ 0.00	1.64/ 0.00	ns
$T_{MMCMDCK\_DWE}$/ $T_{MMCMCKD\_DWE}$	DWE Setup/Hold time	1.25/ 0.00	1.40/ 0.00	1.63/ 0.00	1.64/ 0.00	ns
$T_{MMCMCKO\_DO}$	CLK to out of DO(3)	2.60	3.02	3.64	3.68	ns
$T_{MMCMCKO\_DRDY}$	CLK to out of DRDY	0.32	0.34	0.38	0.38	ns

Notes:

1. To support longer delays in configuration, use the design solutions described in UG360: *Virtex-6 FPGA Configuration User Guide*.
2. Only during configuration, the last edge is determined by a weak pull-up/pull-down resistor in the I/O.
3. DO will hold until next DRP operation.

Clock Buffers and Networks

Table 60: **Global Clock Switching Characteristics (Including BUFGCTRL)**

Symbol	Description	Devices	Speed Grade				Units
			-3	-2	-1	-1L	
T_{BCCCK_CE}/T_{BCCKC_CE}(1)	CE pins Setup/Hold	All	0.11/ 0.00	0.13/ 0.00	0.16/ 0.00	0.13/ 0.00	ns
T_{BCCCK_S}/T_{BCCKC_S}(1)	S pins Setup/Hold	All	0.11/ 0.00	0.13/ 0.00	0.16/ 0.00	0.13/ 0.00	ns
T_{BCCKO_O}(2)	BUFGCTRL delay from I0/I1 to O	All	0.07	0.08	0.10	0.10	ns
Maximum Frequency							
F_{MAX}	Global clock tree (BUFG)	All except LX760	800	750	700	667	MHz
		LX760	N/A	700	700	667	MHz

Notes:

1. T_{BCCCK_CE} and T_{BCCKC_CE} must be satisfied to assure glitch-free operation of the global clock when switching between clocks. These parameters do not apply to the BUFGMUX_VIRTEX4 primitive that assures glitch-free operation. The other global clock setup and hold times are optional; only needing to be satisfied if device operation requires simulation matches on a cycle-for-cycle basis when switching between clocks.
2. T_{BGCKO_O} (BUFG delay from I0 to O) values are the same as T_{BCCKO_O} values.

Table 61: **Input/Output Clock Switching Characteristics (BUFIO)**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T_{BIOCKO_O}	Clock to out delay from I to O	0.14	0.16	0.18	0.21	ns
Maximum Frequency						
F_{MAX}	I/O clock tree (BUFIO)	800	800	710	710	MHz

Table 62: **Regional Clock Switching Characteristics (BUFR)**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
T_{BRCKO_O}	Clock to out delay from I to O	0.56	0.62	0.73	0.82	ns
$T_{BRCKO\_O\_BYP}$	Clock to out delay from I to O with Divide Bypass attribute set	0.28	0.31	0.36	0.41	ns

Table 64: **MMCM Specification *(Cont'd)***

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
$RST_{MINPULSE}$	Minimum Reset Pulse Width	1.5	1.5	1.5	1.5	ns
F_{PFDMAX}	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to High or Optimized(9)	550	500	450	450	MHz
	Maximum Frequency at the Phase Frequency Detector with Bandwidth Set to Low	300	300	300	300	MHz
F_{PFDMIN}	Minimum Frequency at the Phase Frequency Detector with Bandwidth Set to High or Optimized	135	135	135	135	MHz
	Minimum Frequency at the Phase Frequency Detector with Bandwidth Set to Low	10	10	10	10	MHz
$T_{FBDELAY}$	Maximum Delay in the Feedback Path	3 ns Max or one CLKIN cycle				
$T_{MMCMDCK\_PSEN}$/ $T_{MMCMCKD\_PSEN}$	Setup and Hold of Phase Shift Enable	1.04 0.00	1.04 0.00	1.04 0.00	1.04 0.00	ns
$T_{MMCMDCK\_PSINCDEC}$/ $T_{MMCMCKD\_PSINCDEC}$	Setup and Hold of Phase Shift Increment/Decrement	1.04 0.00	1.04 0.00	1.04 0.00	1.04 0.00	ns
$T_{MMCMCKO\_PSDONE}$	Phase Shift Clock-to-Out of PSDONE	0.32	0.34	0.38	0.38	ns

Notes:

1. When DIVCLK_DIVIDE = 3 or 4, F_{INMAX} is 315 MHz.
2. This duty cycle specification does not apply to the GTH_QUAD (GTH) to MMCM connection. The GTH transceivers drive the MMCMs at the following maximum frequencies: 323 MHz for -1 speed grade devices, 350 MHz for -2 speed grade devices, or 350 MHz for -3 speed grade devices.
3. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
4. The static offset is measured between any MMCM outputs with identical phase.
5. Values for this parameter are available in the Clocking Wizard.
   See http://www.xilinx.com/products/intellectual-property/clocking_wizard.htm.
6. Includes global clock buffer.
7. Calculated as $F_{VCO}/128$ assuming output duty cycle is 50%.
8. When CASCADE4_OUT = TRUE, F_{OUTMIN} is 0.036 MHz.
9. In ISE software 12.3 (or earlier versions supporting the Virtex-6 family), the phase frequency detector Optimized bandwidth setting is equivalent to the High bandwidth setting. Starting with ISE software 12.4, the Optimized bandwidth setting is automatically adjusted to Low when the software can determine that the phase frequency detector input is less than 135 MHz.

Virtex-6 Device Pin-to-Pin Input Parameter Guidelines

All devices are 100% functionally tested. The representative values for typical pin locations and normal clock loading are listed in Table 68. Values are expressed in nanoseconds unless otherwise noted.

Table 68: **Global Clock Input Setup and Hold Without MMCM**

Symbol	Description	Device	Speed Grade				Units
			-3	-2	-1	-1L	
Input Setup and Hold Time Relative to Global Clock Input Signal for LVCMOS25 Standard.(1)							
T_{PSFD}/ T_{PHFD}	Full Delay (Legacy Delay or Default Delay) Global Clock Input and IFF(2) without MMCM	XC6VLX75T	1.33/ 0.03	1.44/ 0.03	1.75/ 0.03	2.18/ –0.22	ns
		XC6VLX130T	1.31/ –0.08	1.54/ –0.08	1.88/ –0.08	2.31/ –0.12	ns
		XC6VLX195T	1.36/ –0.11	1.60/ –0.11	1.97/ –0.11	2.40/ –0.25	ns
		XC6VLX240T	1.36/ –0.11	1.60/ –0.11	1.97/ –0.11	2.40/ –0.25	ns
		XC6VLX365T	1.79/ –0.28	1.87/ –0.28	2.17/ –0.28	2.48/ –0.24	ns
		XC6VLX550T	N/A	2.22/ –0.12	2.36/ –0.12	2.77/ –0.26	ns
		XC6VLX760	N/A	2.19/ –0.24	2.35/ –0.24	2.71/ –0.21	ns
		XC6VSX315T	1.75/ –0.09	1.85/ –0.09	2.06/ –0.09	2.47/ –0.24	ns
		XC6VSX475T	N/A	2.14/ –0.14	2.31/ –0.14	2.71/ –0.30	ns
		XC6VHX250T	1.93/ –0.22	2.04/ –0.22	2.25/ –0.22	N/A	ns
		XC6VHX255T	1.81/ –0.33	2.11/ –0.33	2.56/ –0.33	N/A	ns
		XC6VHX380T	1.93/ –0.11	2.04/ –0.11	2.25/ –0.11	N/A	ns
		XC6VHX565T	N/A	2.20/ –0.12	2.39/ –0.12	N/A	ns
		XQ6VLX130T	N/A	1.54/ –0.08	1.88/ –0.08	2.31/ –0.12	ns
		XQ6VLX240T	N/A	1.60/ –0.11	1.97/ –0.11	2.40/ –0.25	ns
		XQ6VLX550T	N/A	N/A	2.36/ –0.12	2.77/ –0.26	ns
		XQ6VSX315T	N/A	1.85/ –0.09	2.06/ –0.09	2.47/ –0.24	ns
		XQ6VSX475T	N/A	N/A	2.31/ –0.14	2.71/ –0.30	ns

Notes:

1. Setup and Hold times are measured over worst case conditions (process, voltage, temperature). Setup time is measured relative to the Global Clock input signal using the slowest process, highest temperature, and lowest voltage. Hold time is measured relative to the Global Clock input signal using the fastest process, lowest temperature, and highest voltage.
2. IFF = Input Flip-Flop or Latch
3. A Zero "0" Hold Time listing indicates no hold time or a negative hold time. Negative values can not be guaranteed "best-case", but if a "0" is listed, there is no positive hold time.

Table 73: **Sample Window**

Symbol	Description	Device	Speed Grade				Units
			-3	-2	-1	-1L	
T_{SAMP}	Sampling Error at Receiver Pins(1)	All	510	560	610	670	ps
T_{SAMP_BUFIO}	Sampling Error at Receiver Pins using BUFIO(2)	All	300	350	400	440	ps

Notes:

1. This parameter indicates the total sampling error of Virtex-6 FPGA DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the MMCM to capture the DDR input registers' edges of operation. These measurements include:
   - CLK0 MMCM jitter
   - MMCM accuracy (phase offset)
   - MMCM phase shift resolution

   These measurements do not include package or clock tree skew.
2. This parameter indicates the total sampling error of Virtex-6 FPGA DDR input registers, measured across voltage, temperature, and process. The characterization methodology uses the BUFIO clock network and IODELAY to capture the DDR input registers' edges of operation. These measurements do not include package or clock tree skew.

Table 74: **Pin-to-Pin Setup/Hold and Clock-to-Out**

Symbol	Description	Speed Grade				Units
		-3	-2	-1	-1L	
Data Input Setup and Hold Times Relative to a Forwarded Clock Input Pin Using BUFIO						
T_{PSCS}/T_{PHCS}	Setup/Hold of I/O clock	–0.28/1.09	–0.28/1.16	–0.28/1.33	–0.18/1.79	ns
Pin-to-Pin Clock-to-Out Using BUFIO						
$T_{ICKOFCS}$	Clock-to-Out of I/O clock	4.22	4.59	5.22	5.63	ns

Revision History

The following table shows the revision history for this document:

Date	Version	Description of Revisions
06/24/09	1.0	Initial Xilinx release.
07/16/09	1.1	Revised the maximum V_{CCAUX} and V_{IN} numbers in Table 2, page 2. Removed empty column from Table 3, page 3. Revised specifications on Table 20, page 13. Updated Table 38, page 22 and added notes 1 and 2. Revised T_{DLYCCO_RDY}, $T_{IDELAYCTRL\_RPW}$, and $T_{IDELAYPAT\_JIT}$ in Table 53, page 41. Updated Table 58, page 46 to more closely match the DSP48E1 speed specifications. Updated T_{TAPTCK}/T_{TCKTAP} in Table 59, page 49. Updated XC6VLX130T parameters in Table 68 through Table 70, page 59.
08/19/09	1.2	Added values for -1L voltages and speed grade in all pertinent tables. Added V_{FS} and notes to Table 1 and Table 2. Removed DV_{PPIN} from the example in Figure 2. Added networking applications to Table 41, page 25. Changed and added to the block RAM F_{MAX} section in Table 57, page 44 including removing Note 12. Changed F_{PFDMAX} values and corrected units for $T_{STATPHAOFFSET}$ and $T_{OUTDUTY}$ in Table 64, page 52. Updated Table 71, page 60.
09/16/09	2.0	Added Virtex-6 HXT devices to entire document including GTH Transceiver Specifications. Updated speed specifications as described in Switching Characteristics, includes changes in Table 51, Table 57, Table 58, and Table 66 through Table 70. Comprehensive changes to Table 14, Table 15, and Table 16. Added conditions to D_{VPPOUT} and revised description of T_{OSKEW} in Table 17. Removed V_{ISE} specification and note from Table 18. Added note 3 to Table 23. Updated note 3 in Table 24. Updated LVCMOS25 delays in Table 44. Updated specification for T_{IOTPHZ} in Table 46. Removed $T_{BUFHSKEW}$ from Table 71, page 60 and added values for $T_{BUFIOSKEW}$. Added values in Table 74.